

A SEMICONDUCTOR DEVICE HAVING A GHOST
SOURCE/DRAIN REGION AND A METHOD OF MANUFACTURE THEREFOR

ABSTRACT OF THE DISCLOSURE

The present invention provides a semiconductor device and a method of manufacture therefor. The semiconductor device includes a channel region located in a semiconductor substrate and a trench located adjacent a side of the channel region. The semiconductor device further includes an isolation structure located in the trench, and a source/drain region located over the isolation structure.